

N-Channel Power MOSFET

900V, 4A, 4.0Ω

FEATURES

- Low $R_{DS(ON)}$ 4 Ω (Max.)
- Low gate charge typical @ 25nC (Typ.)
- Improve dV/dt capability

KEY PERFORMANCE PARAMETERS				
PARAMETER	VALUE UNIT			
V_{DS}	900	V		
R _{DS(on)} (max)	4	Ω		
Q_g	25	nC		

APPLICATION

• High efficiency switch mode power Supply

• Lighting



Notes: Moisture sensitivity level: level 3. Per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T _A =25°C unless otherwise noted)					
PARAMETER	SYMBOL	TO-220	ITO-220	UNIT	
Drain-Source Voltage	V_{DS}	900 \		V	
Gate-Source Voltage	V_{GS}	±30 V		V	
Continuous Drain Current (Note 4) T _C = 25°C	I _D	4	4*	^	
T _C = 100°C		2.2	2.2*	Α	
Pulsed Drain Current (Note 2)	I _{DM}	16	16 *	Α	
Total Power Dissipation @ T _C = 25°C	P_{DTOT}	123	38.7	W	
Single Pulsed Avalanche Energy (Note 3)	E _{AS}	474		mJ	
Single Pulsed Avalanche Current (Note 3)	I _{AS}	4		Α	
Repetitive Avalanche Energy ^(Note 2)	E_AR	12	2.3	mJ	
Peak Diode Recovery (Note 7)	dV/dt	4.	.5	V	
Operating Junction and Storage Temperature Range	T_J,T_STG	- 55 to	+150	°C	

THERMAL PERFORMANCE				
PARAMETER	SYMBOL	TO-220	ITO-220	UNIT
Junction to Case Thermal Resistance	R _{eJC}	1.01	3.23	°C/W
Junction to Ambient Thermal Resistance	R _{OJA}	62.5		°C/W

Notes: $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. $R_{\Theta JA}$ is guaranteed by design while $R_{\Theta CA}$ is determined by the user's board design. $R_{\Theta JA}$ shown below for single device operation on FR-4 PCB in still air.



ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static (Note 4)						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV _{DSS}	900			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	2		4	V
Gate Body Leakage	$V_{GS} = \pm 30V, V_{DS} = 0V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 900V, V_{GS} = 0V$	I _{DSS}		1	10	μA
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 2.0A$	R _{DS(on)}		3.2	4.0	Ω
Forward Transconductance	$V_{DS} = 30V, I_{D} = 2.0A$	g fs		6		S
Dynamic (Note 5)						
Total Gate Charge	7001/ 1 4 04	Q_g		25		
Gate-Source Charge	$V_{DS} = 720V, I_D = 4.0A,$	Q_{gs}	(4.8		nC
Gate-Drain Charge	V _{GS} = 10V	Q_{gd}		10.2		
Input Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$	C _{iss}		955		
Output Capacitance	f = 1.0MHz	Coss		80		pF
Gate Resistance	F = 1MHz, open drain	R_g		-	4	Ω
Switching (Note 6)						
Turn-On Delay Time		t _{d(on)}		49		
Turn-On Rise Time	$V_{DD} = 450V,$ $R_{GEN} = 25\Omega,$ $I_{D} = 4.0A, V_{GS} = 10V,$	t _r		38		
Turn-Off Delay Time		t _{d(off)}		146		ns
Turn-Off Fall Time		t _f		50		
Source-Drain Diode (Note 4)						
Forward On Voltage	$I_S = 4.0A$, $V_{GS} = 0V$	V_{SD}		-	1.5	V
Reverse Recovery Time	$V_{GS} = 0V$, $I_S = 4A$	t _{rr}		487		ns
Reverse Recovery Charge	$dI_F/dt = 100A/\mu s$	Q _{rr}		2.8		μC

Notes:

- Current limited by package.
- Pulse width limited by the maximum junction temperature.
- 3. L = 56mH, I_{AS} = 4.0A, V_{DD} = 50V, R_{G} = 25 Ω , Starting T_{J} = 25 $^{\circ}$ C.
- 4. Pulse test: PW \leq 300 μ s, duty cycle \leq 2%.
- 5. For DESIGN AID ONLY, not subject to production testing.
- 6. Switching time is essentially independent of operating temperature.
- 7. $I_{SD} \le 4A$, $dI/dt \le 200A/uS$, $V_{DD} \le BV_{DSS}$, Starting $T_J = 25^{\circ}C$.



ORDERING INFORMATION

PART NO.	PACKAGE	PACKING
TSM4N90CZ C0G	TO-220	50pcs / Tube
TSM4N90CI C0G	ITO-220	50pcs / Tube

Note:

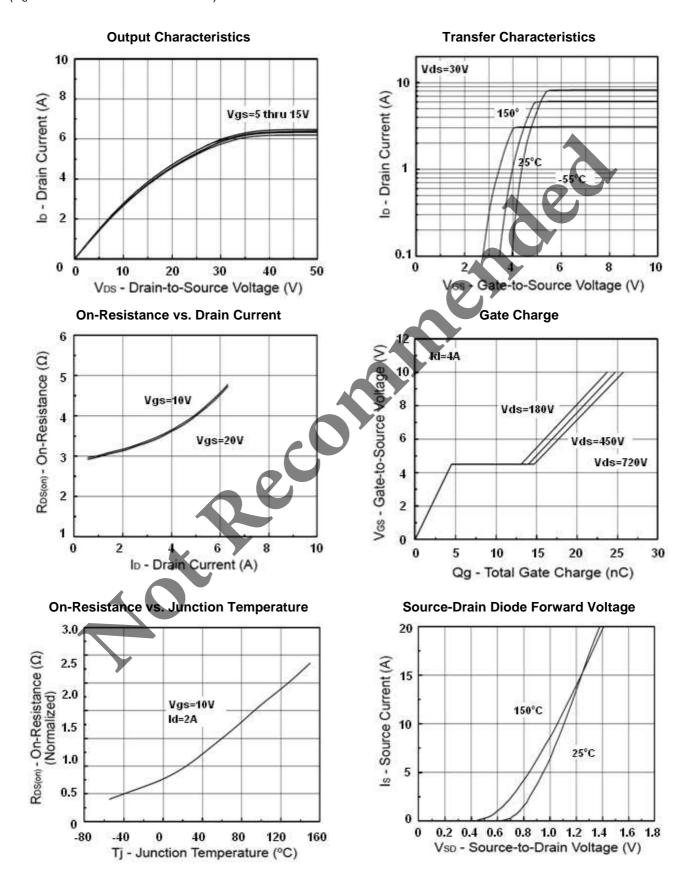
- 1. Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition





CHARACTERISTICS CURVES

 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$

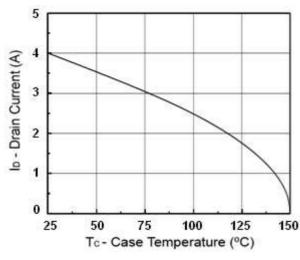




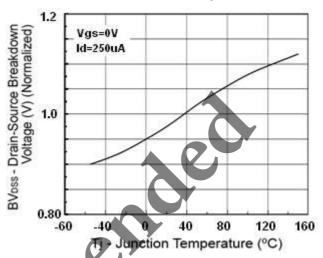
CHARACTERISTICS CURVES

 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$

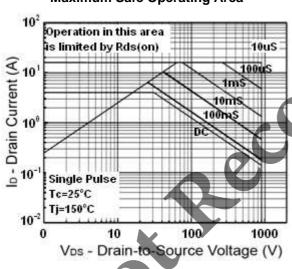
Drain Current vs. Case Temperature



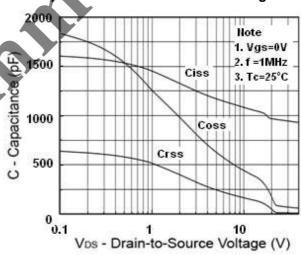
BV_{DSS} vs. Junction Temperature



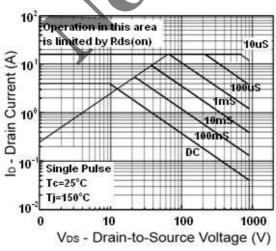
Maximum Safe Operating Area



Capacitance vs. Drain-Source Voltage



Maximum Safe Operating Area (ITO-220)

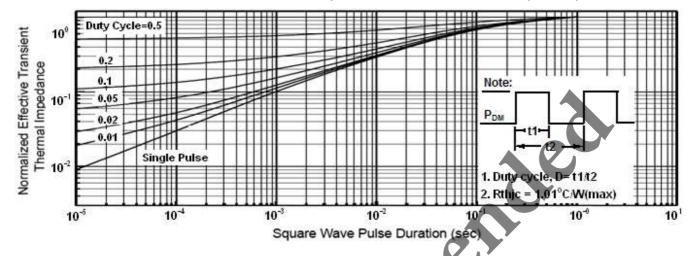




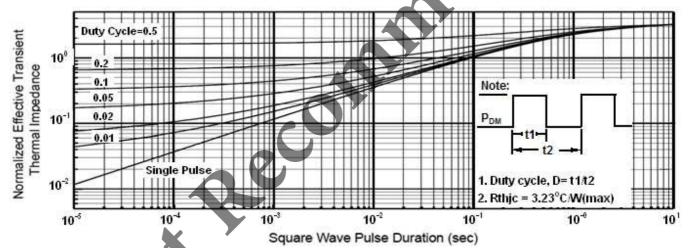
CHARACTERISTICS CURVES

 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$

Normalized Thermal Transient Impedance, Junction-to-Ambient (TO-220)

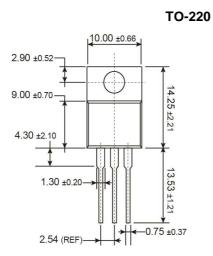


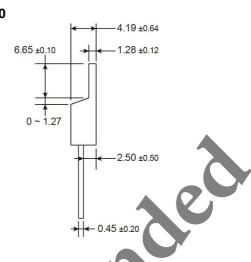
Normalized Thermal Transient Impedance, Junction-to-Ambient (ITO-220)





PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)





MARKING DIAGRAM



Y = Year Code

M = Month Code for Halogen Free Product

O =Jan P =Feb **Q** =Mar =Apr

S =May T =Jun **U** =Jul

W =Sep X =Oct



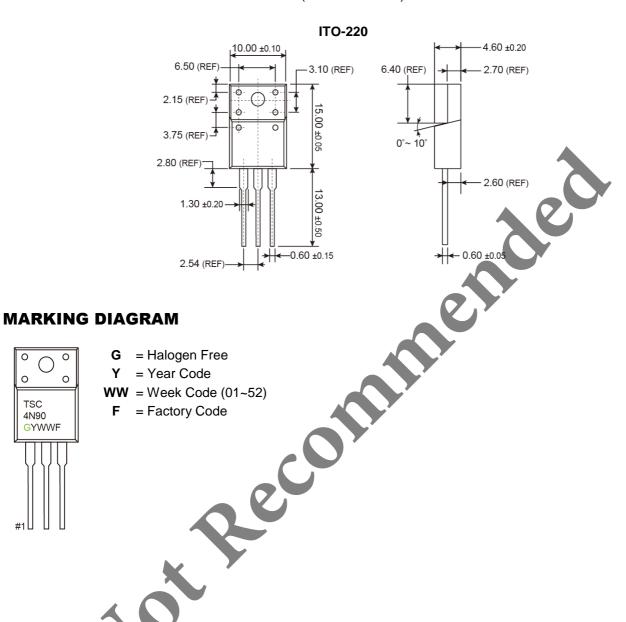
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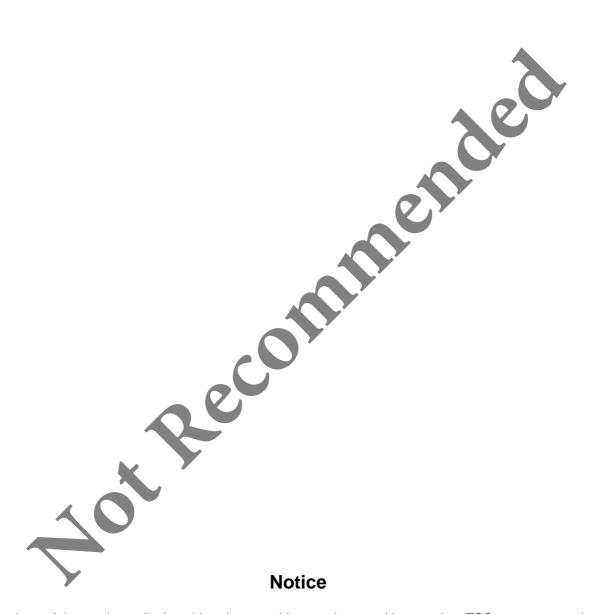
TSC

4N90 GYWWF

PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)







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